

isc Silicon PNP Power Transistor

2SB980

DESCRIPTION

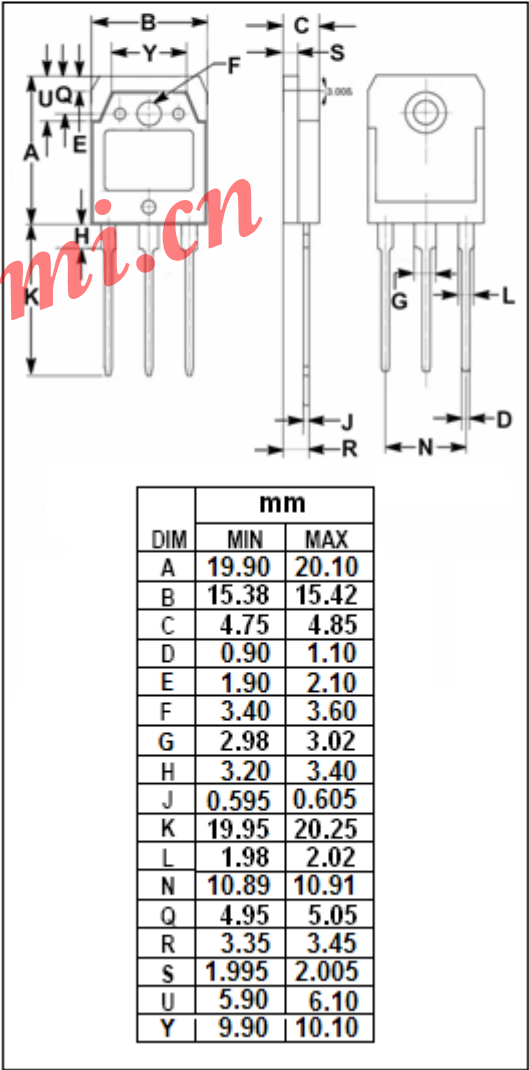
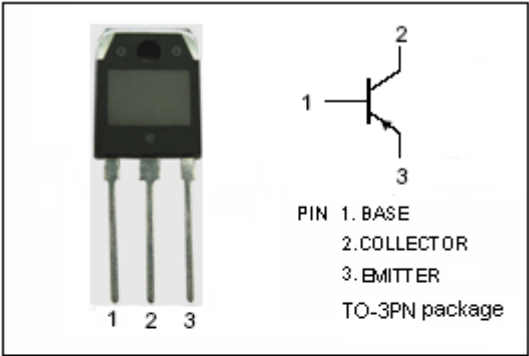
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation

APPLICATIONS

- Designed for high power amplifications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-6	A
I_{CP}	Collector Current-Pulse	-10	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	70	W
	Collector Power Dissipation @ $T_a=25^{\circ}C$	3	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB980****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -4A$; $I_B = -0.4A$			-2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C = -4A$; $V_{CE} = -5V$			-1.8	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120V$; $I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3V$; $I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -20mA$; $V_{CE} = -5V$	20			
h_{FE-2}	DC Current Gain	$I_C = -1A$; $V_{CE} = -5V$	60		200	
h_{FE-3}	DC Current Gain	$I_C = -4A$; $V_{CE} = -5V$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5A$; $V_{CE} = -5V$; $f = 1MHz$		20		MHz
C_{OB}	Output Capacitance	$I_E = 0$; $V_{CB} = -10V$; $f = 1MHz$		150		pF

◆ **h_{FE-2} Classifications**

Q	S	P
60-120	80-160	100-200